

Characterization and Failure Mode Analysis of Cascode GaN HEMT

Zhengyang Liu

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Fred C. Lee, Chair
Qiang Li
Rolando Burgos

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Figure 1.8 Percentage of on-resistance from Si MOSFET to the cascode device [5]
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[5] Alex Lidow, Michael de Rooij, Johan Strydom, David Reusch, Efficient Power Conversion Corp. “GaN Transistors for Efficient Power Conversion”, APEC 2013 educational seminar S7, pp. 16.